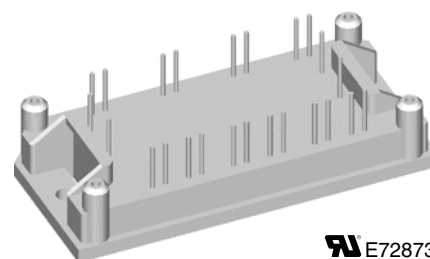
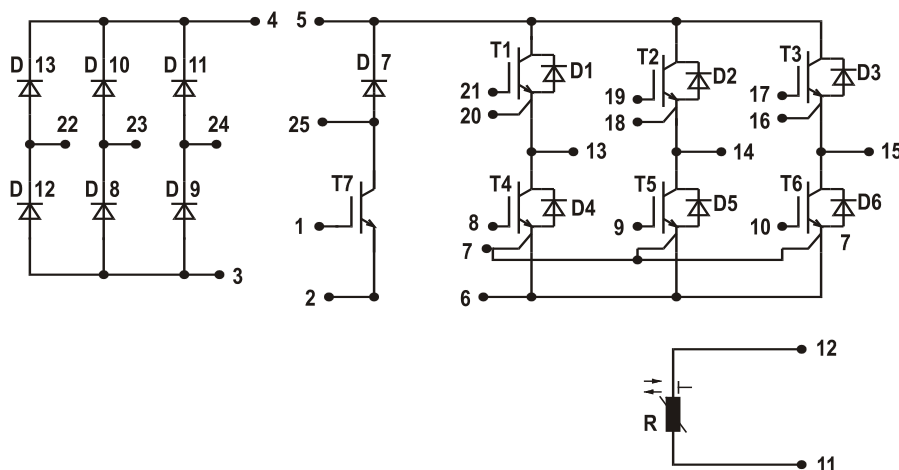


Converter - Brake - Inverter **Module** (CBI 1) **NPT IGBT**

Three Phase Rectifier	Brake Chopper	Three Phase Inverter
$V_{RRM} = 1600 \text{ V}$	$V_{CES} = 1200 \text{ V}$	$V_{CES} = 1200 \text{ V}$
$I_{DAVM25} = 130 \text{ A}$	$I_{C25} = 19 \text{ A}$	$I_{C25} = 19 \text{ A}$
$I_{FSM} = 300 \text{ A}$	$V_{CE(sat)} = 2.9 \text{ V}$	$V_{CE(sat)} = 2.9 \text{ V}$

Part name (Marking on product)

MUBW15-12A6K



E72873

Pin configuration see outlines.

Features:

- High level of integration - only one power semiconductor module required for the whole drive
- Inverter with NPT IGBTs
- low saturation voltage
- positive temperature coefficient
- fast switching
- short tail current
- Epitaxial free wheeling diodes with hiperfast and soft reverse recovery
- Industry standard package with insulated copper base plate and soldering pins for PCB mounting
- Temperature sense included

Application:

- AC motor drives with
- Input from single or three phase grid
 - Three phase synchronous or asynchronous motor
 - Electric braking operation

Package:

- UL registered
- Industry standard E1-pack

Output Inverter T1 - T6

				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V _{CES}	collector emitter voltage	T _{VJ} = 25°C to 150°C			1200	V
V _{GES}	max. DC gate voltage	continuous			±20	V
V _{GEM}	max. transient collector gate voltage	transient			±30	V
I _{C25}	collector current	T _C = 25°C			19	A
I _{C80}		T _C = 80°C			13	A
P _{tot}	total power dissipation	T _C = 25°C			90	W
V _{CE(sat)}	collector emitter saturation voltage	I _C = 15 A; V _{GE} = 15 V	T _{VJ} = 25°C T _{VJ} = 125°C	3.0 3.5	3.4	V
V _{GE(th)}	gate emitter threshold voltage	I _C = 0.35 mA; V _{GE} = V _{CE}	T _{VJ} = 25°C	4.5	6.5	V
I _{CES}	collector emitter leakage current	V _{CE} = V _{CES} ; V _{GE} = 0 V	T _{VJ} = 25°C T _{VJ} = 125°C	1.3	0.6	mA mA
I _{GES}	gate emitter leakage current	V _{CE} = 0 V; V _{GE} = ±20 V			100	nA
C _{ies}	input capacitance	V _{CE} = 25 V; V _{GE} = 0 V; f = 1 MHz		600		pF
Q _{G(on)}	total gate charge	V _{CE} = 600 V; V _{GE} = 15 V; I _C = 10 A		45		nC
t _{d(on)}	turn-on delay time	} inductive load V _{CE} = 600 V; I _C = 10 A V _{GE} = ±15 V; R _G = 82 Ω	T _{VJ} = 125°C	50		ns
t _r	current rise time			40		ns
t _{d(off)}	turn-off delay time			290		ns
t _f	current fall time			60		ns
E _{on}	turn-on energy per pulse			1.2		mJ
E _{off}	turn-off energy per pulse			1.1		mJ
I _{CM}	reverse bias safe operating area	RBSOA; V _{GE} = ±15 V; R _G = 82 Ω L = 100 μH; clamped induct. load V _{CEmax} = V _{CES} - L _S ·di/dt	T _{VJ} = 125°C	26		A
t _{SC} (SCSOA)	short circuit safe operating area	V _{CE} = 720 V; V _{GE} = ±15 V; R _G = 82 Ω; non-repetitive	T _{VJ} = 125°C	10		μs
R _{thJC}	thermal resistance junction to case	(per IGBT)			1.35	K/W
R _{thCH}	thermal resistance case to heatsink	(per IGBT)		0.5		K/W

Output Inverter D1 - D6

				Ratings		
Symbol	Definitions	Conditions	min.	typ.	max.	Unit
V_{RRM}	<i>max. repetitive reverse voltage</i>	$T_{VJ} = 150^{\circ}\text{C}$			1200	V
I_{F25}	<i>forward current</i>	$T_C = 25^{\circ}\text{C}$			26	A
I_{F80}		$T_C = 80^{\circ}\text{C}$			17	A
V_F	<i>forward voltage</i>	$I_F = 30\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.3	3.4	V V
I_{RM}	<i>max. reverse recovery current</i>	$\left. \begin{array}{l} V_R = 600\text{ V} \\ di_F/dt = -400\text{ A}/\mu\text{s} \\ I_F = 15\text{ A}; V_{GE} = 0\text{ V} \end{array} \right\}$	$T_{VJ} = 100^{\circ}\text{C}$	16		A
t_{rr}	<i>reverse recovery time</i>			130		ns
$E_{rec(off)}$	<i>reverse recovery energy</i>			tbd		μJ
R_{thJC}	<i>thermal resistance junction to case</i>	(per diode)			1.6	K/W
R_{thCH}	<i>thermal resistance case to heatsink</i>	(per diode)		0.55		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Brake Chopper T7

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$ to 150°C			1200		V
V_{GES}	max. DC gate voltage	continuous			± 20		V
V_{GEM}	max. transient collector gate voltage	transient			± 30		V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			19		A
I_{C80}		$T_C = 80^{\circ}\text{C}$			13		A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			90		W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 15\text{ A}; V_{GE} = 15\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	2.9 3.5	3.4	V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.4\text{ mA}; V_{GE} = V_{CE}$	4.5	$T_{VJ} = 25^{\circ}\text{C}$		6.5	V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.8	0.5	mA mA
I_{GES}	gate emitter leakage current	$V_{CE} = 0\text{ V}; V_{GE} = \pm 20\text{ V}$			100		nA
C_{ies}	input capacitance	$V_{CE} = 25\text{ V}; V_{GE} = 0\text{ V}; f = 1\text{ MHz}$		600			pF
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 10\text{ A}$		45			nC
$t_{d(on)}$	turn-on delay time	} inductive load $V_{CE} = 600\text{ V}; I_C = 10\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$		$T_{VJ} = 125^{\circ}\text{C}$	45		ns
t_r	current rise time				40		ns
$t_{d(off)}$	turn-off delay time				290		ns
t_f	current fall time				60		ns
E_{on}	turn-on energy per pulse				1.2		mJ
E_{off}	turn-off energy per pulse				1.1		mJ
I_{CM}	reverse bias safe operating area	RBSOA; $V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$ $L = 100\ \mu\text{H}$; clamped induct. load $V_{CEmax} = V_{CES} - L_S \cdot di/dt$		$T_{VJ} = 125^{\circ}\text{C}$	20		A
t_{SC} (SCSOA)	short circuit safe operating area	$V_{CE} = 720\text{ V}; V_{GE} = \pm 15\text{ V}; R_G = 82\ \Omega$; non-repetitive		$T_{VJ} = 125^{\circ}\text{C}$	10		μs
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.35		K/W
R_{thCH}	thermal resistance case to heatsink	(per IGBT)		0.45			K/W

Brake Chopper D7

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 150^{\circ}\text{C}$			1200		V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			15		A
I_{F80}		$T_C = 80^{\circ}\text{C}$			10		A
V_F	forward voltage	$I_F = 15\text{ A}; V_{GE} = 0\text{ V}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	3.5 2.0		V V
I_R	reverse current	$V_R = V_{RRM}$		$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$	0.2	0.06	mA mA
I_{RM}	max. reverse recovery current	} $V_R = 600\text{ V}; I_F = 10\text{ A}$ $di_F/dt = -400\text{ A}/\mu\text{s}$		$T_{VJ} = 100^{\circ}\text{C}$	13		A
t_{rr}	reverse recovery time				110		ns
R_{thJC}	thermal resistance junction to case	(per diode)			2.5		K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.85			K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

Input Rectifier Bridge D8 - D13

Symbol	Definitions	Conditions	Maximum Ratings		
V _{RRM}	max. repetitive reverse voltage		1600	V	
I _{FAV}	average forward current	sine 180°	T _C = 80°C	31	A
I _{DAVM}	max. average DC output current	rectangular; d = 1/3; bridge	T _C = 80°C	89	A
I _{FSM}	max. surge forward current	t = 10 ms; sine 50 Hz	T _C = 25°C	320	A
P _{tot}	total power dissipation		T _C = 25°C	80	W

Symbol	Conditions	Characteristic Values			
		min.	typ.	max.	
V_F	forward voltage	$I_F = 30\text{ A}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	1.0 1.1	1.35 V
I_R	reverse current	$V_R = V_{RRM}$	$T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	0.4	0.02 mA
R_{thJC}	thermal resistance junction to case	(per diode)	$T_{VJ} = 25^\circ\text{C}$		1.4 K/W
R_{thCH}	thermal resistance case to heatsink	(per diode)		0.45	K/W

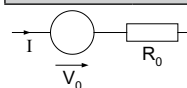
Temperature Sensor NTC

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
R_{25}	resistance	$T_C = 25^\circ\text{C}$	4.45	4.7	5.0	k Ω
$B_{25/85}$				3510		K

Module

Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
T_{VJ}	operating temperature		-40		125	$^\circ\text{C}$
T_{VJM}	max. virtual junction temperature				150	$^\circ\text{C}$
T_{stg}	storage temperature		-40		125	$^\circ\text{C}$
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1\text{ mA}$; 50/60 Hz			2500	V~
M_d	mounting torque	(M4)	2.0		2.2	Nm
d_s	creep distance on surface		12.7			mm
d_A	strike distance through air		12.7			mm
Weight				40		g

Equivalent Circuits for Simulation

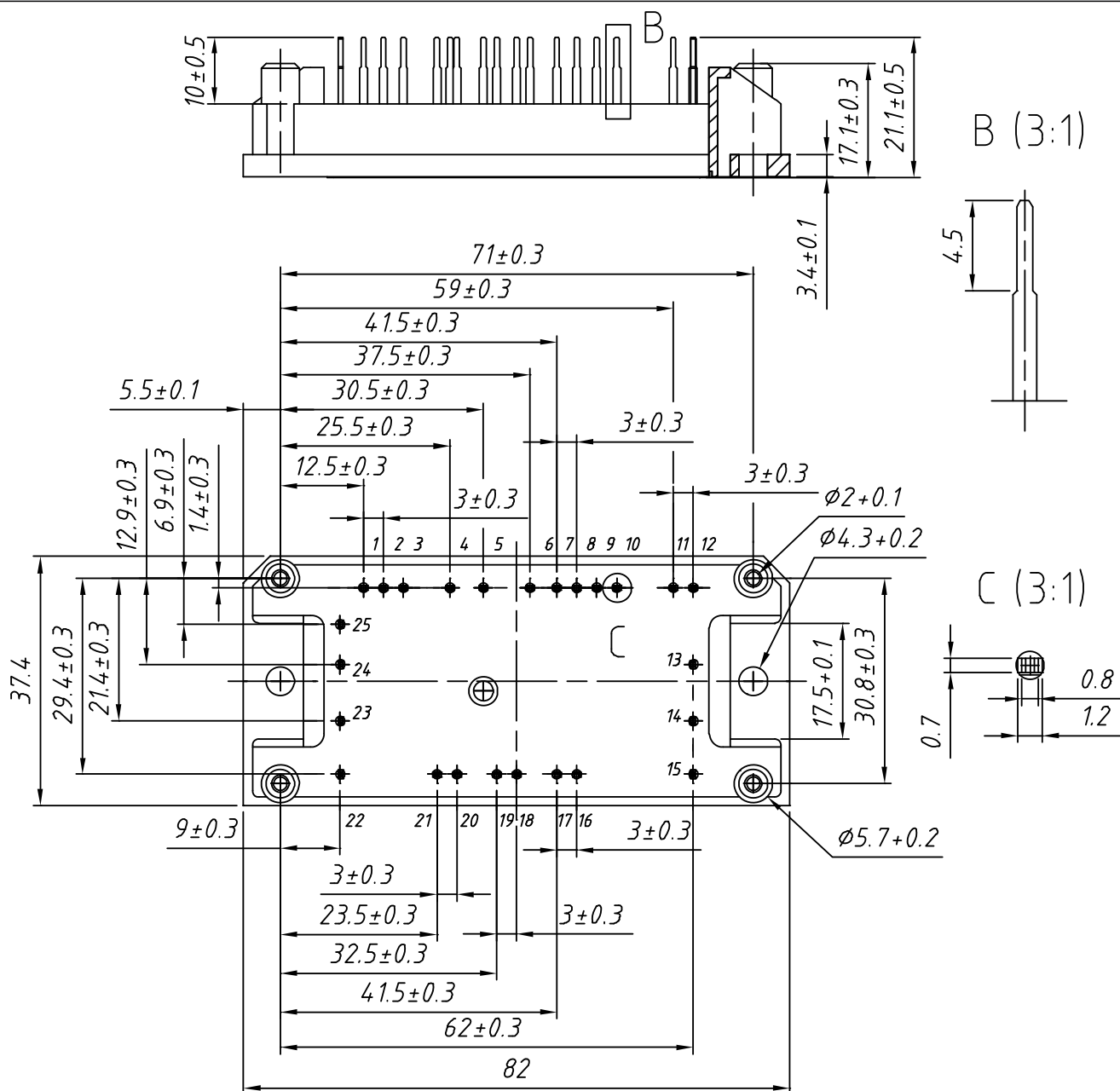


Symbol	Definitions	Conditions	min.	Ratings		Unit
				typ.	max.	
V_0	rectifier diode	D8 - D13	$T_{VJ} = 125^\circ\text{C}$	0.90		V
R_0				9		m Ω
V_0	IGBT	T1 - T6	$T_{VJ} = 125^\circ\text{C}$	1.50		V
R_0				120		m Ω
V_0	free wheeling diode	D1 - D6	$T_{VJ} = 125^\circ\text{C}$	1.46		V
R_0				31		m Ω
V_0	IGBT	T7	$T_{VJ} = 125^\circ\text{C}$	1.50		V
R_0				120		m Ω
V_0	free wheeling diode	D7	$T_{VJ} = 125^\circ\text{C}$	1.46		V
R_0				63		m Ω

$T_C = 25^\circ\text{C}$ unless otherwise stated

Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MUBW 15-12A6K	MUBW15-12A6K	Box	10	499 331

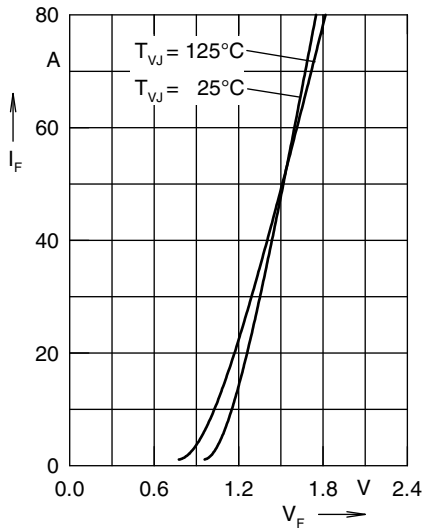


Fig. 1 Forward current versus voltage drop per diode

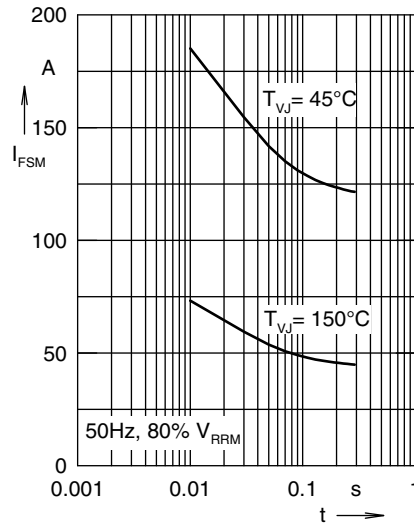


Fig. 2 Surge overload current

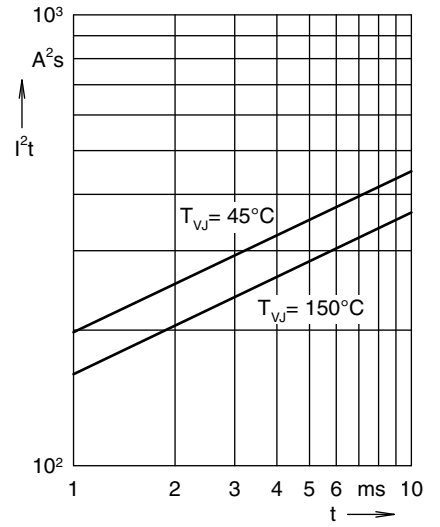


Fig. 3 I_2t versus time per diode

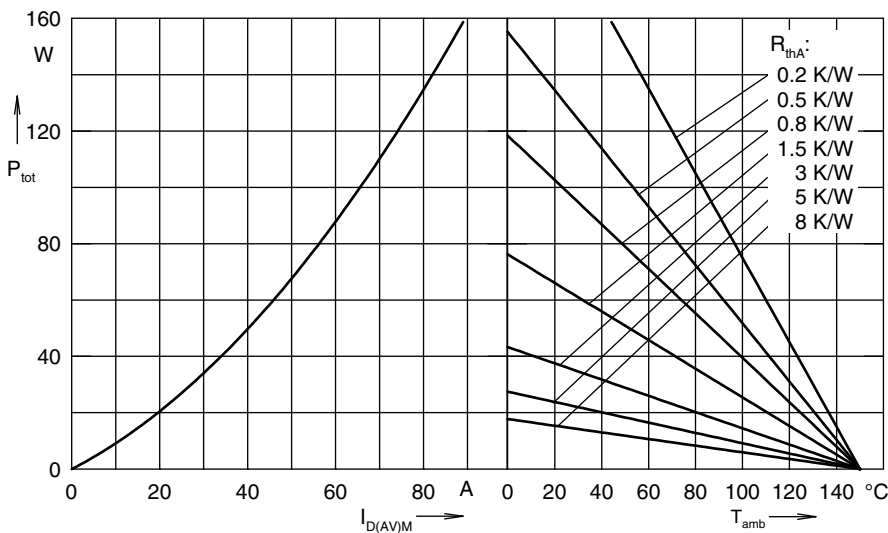


Fig. 4 Power dissipation versus direct output current and ambient temperature, sin 180°

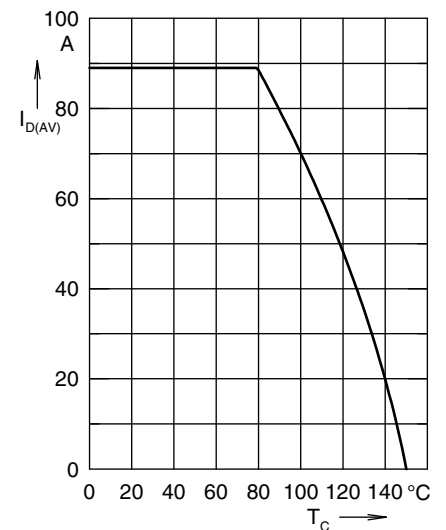


Fig. 5 Max. forward current vs. case temperature

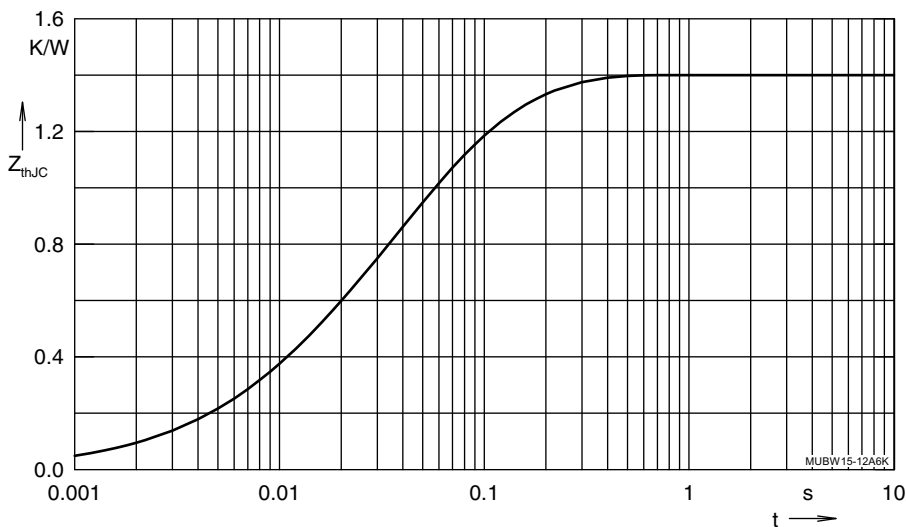


Fig. 6 Transient thermal impedance junction to case

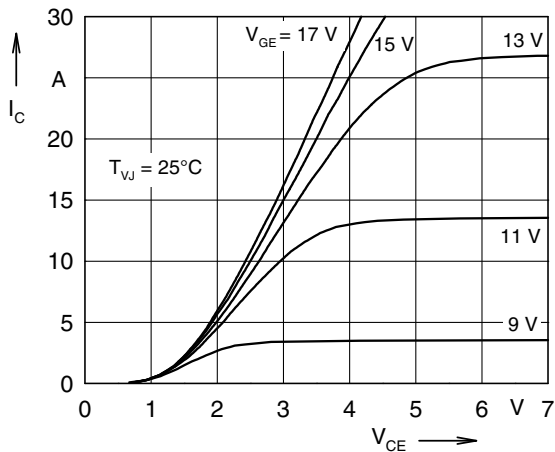


Fig. 7 Typ. output characteristics

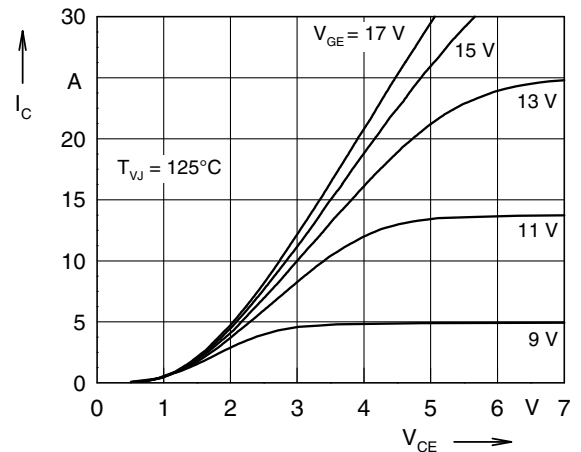


Fig. 8 Typ. output characteristics

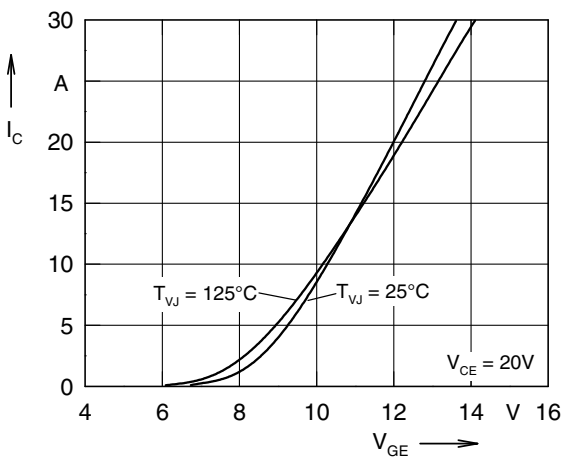


Fig. 9 Typ. transfer characteristics

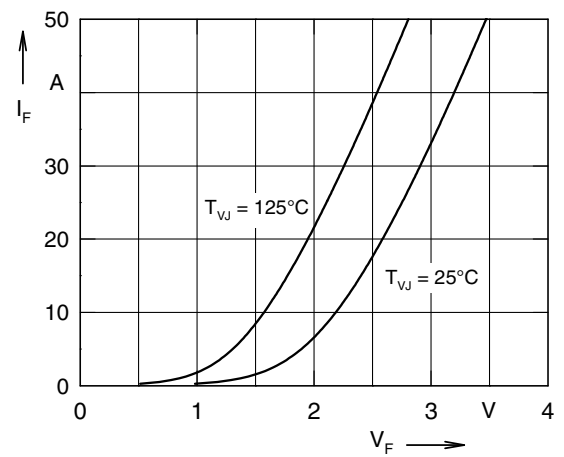


Fig. 10 Typ. forward characteristics of free wheeling diode

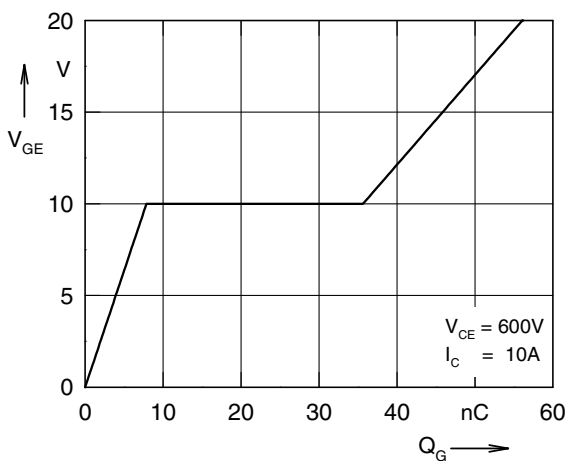


Fig. 11 Typ. turn on gate charge

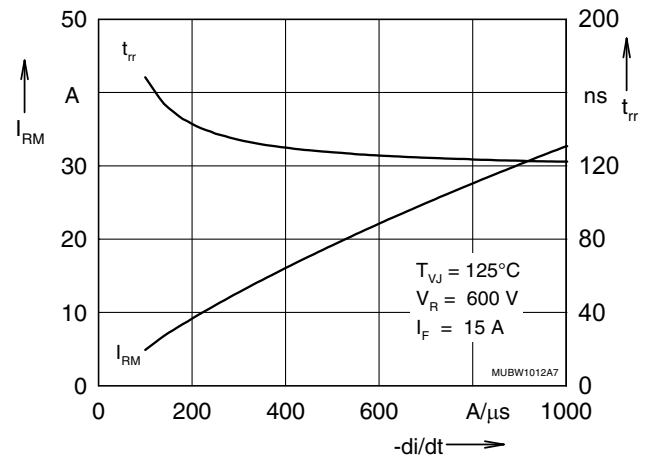


Fig. 12 Typ. turn off characteristics of free wheeling diode

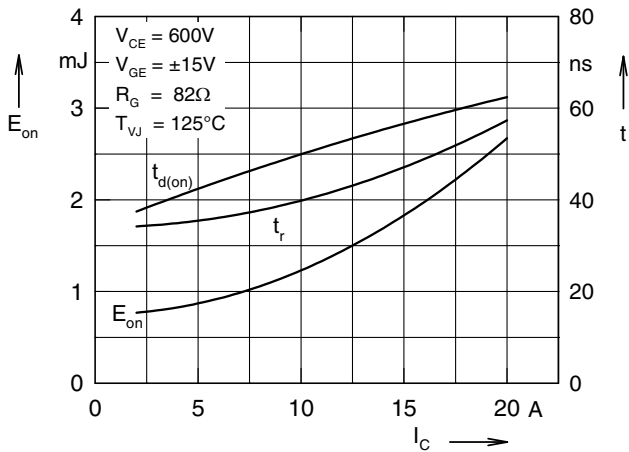


Fig. 13 Typ. turn on energy and switching times versus collector current

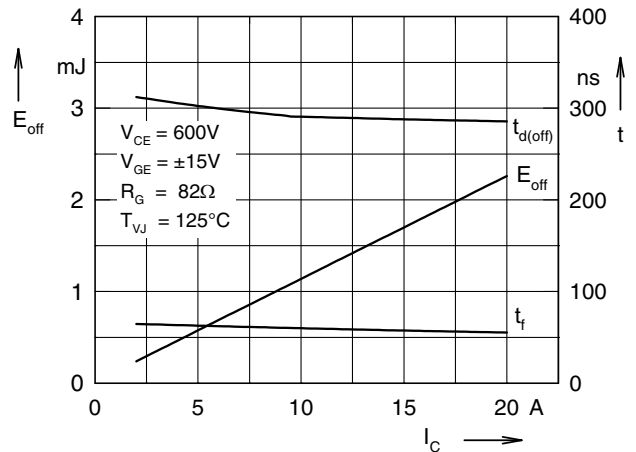


Fig. 14 Typ. turn off energy and switching times versus collector current

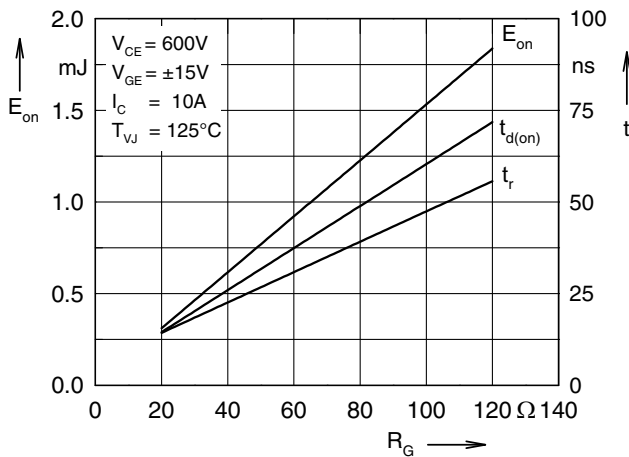


Fig. 15 Typ. turn on energy and switching times versus gate resistor

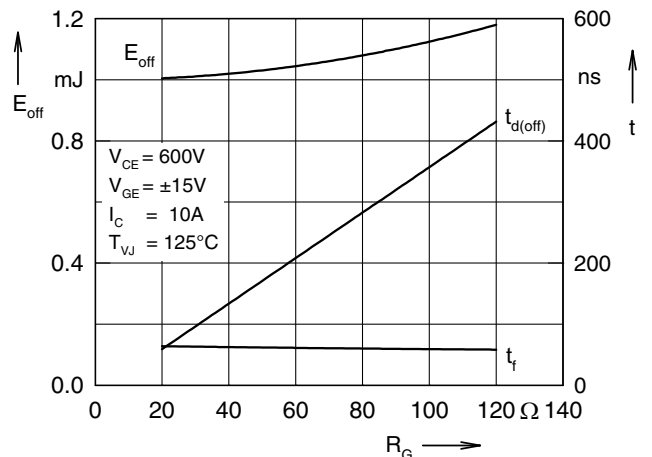


Fig. 16 Typ. turn off energy and switching times versus gate resistor

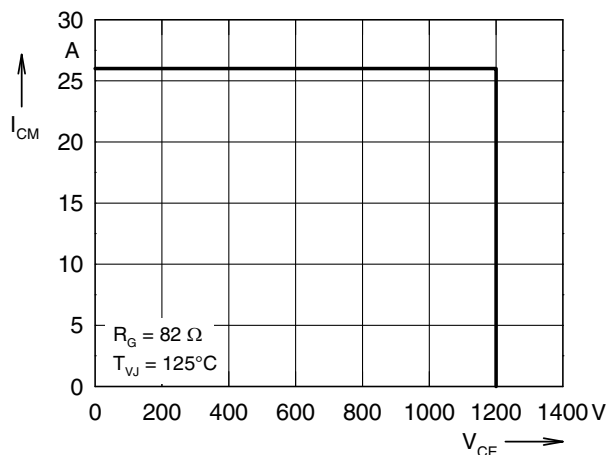


Fig. 17 Reverse biased safe operating area RBSOA

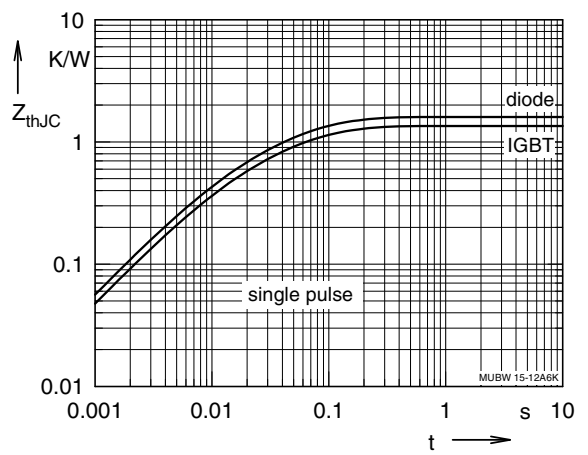


Fig. 18 Typ. transient thermal impedance

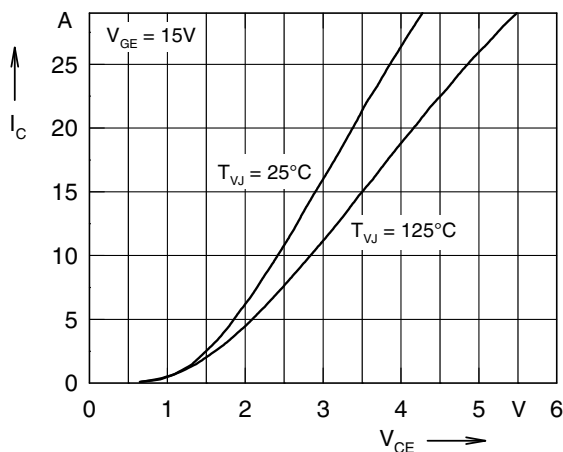


Fig. 19 Typ. output characteristics

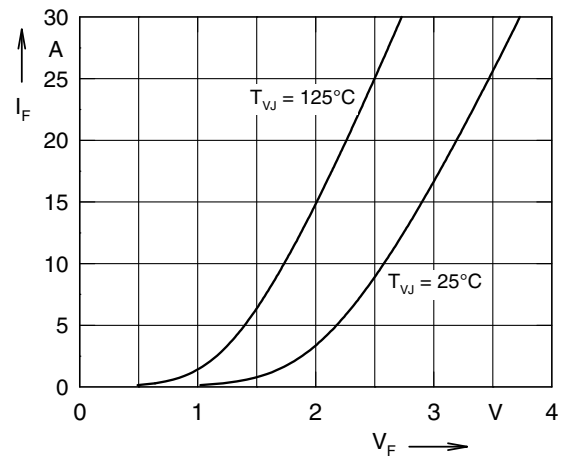


Fig. 20 Typ. forward characteristics of free wheeling diode

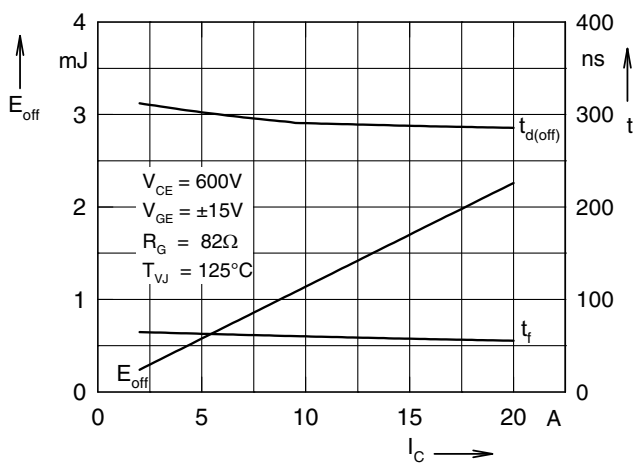


Fig. 21 Typ. turn off energy and switching times versus collector current

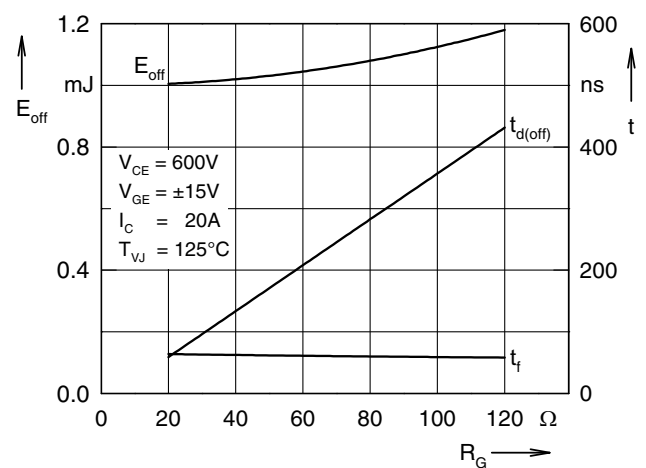


Fig. 22 Typ. turn off energy and switching times versus gate resistor

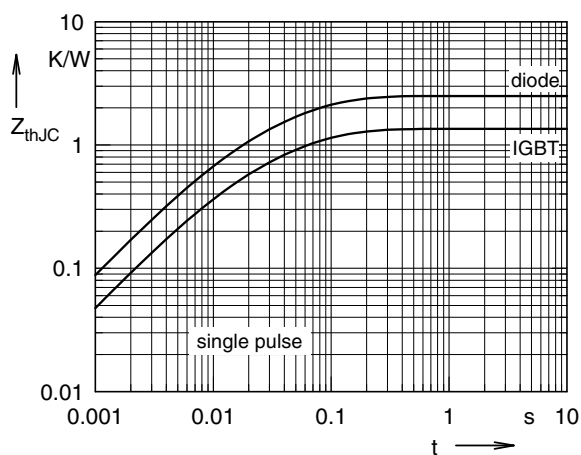


Fig. 23 Typ. transient thermal impedance

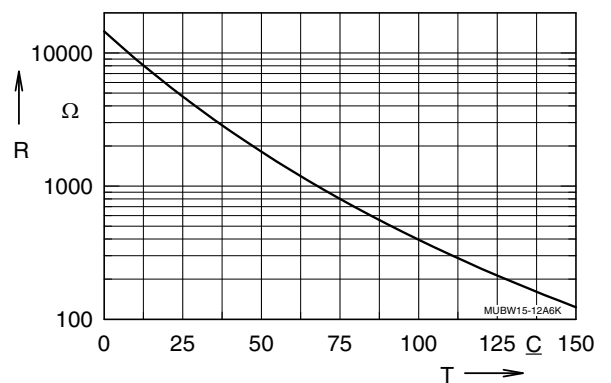


Fig. 24 Typ. thermistor resistance versus temperature